ELECTRONICS, INC.
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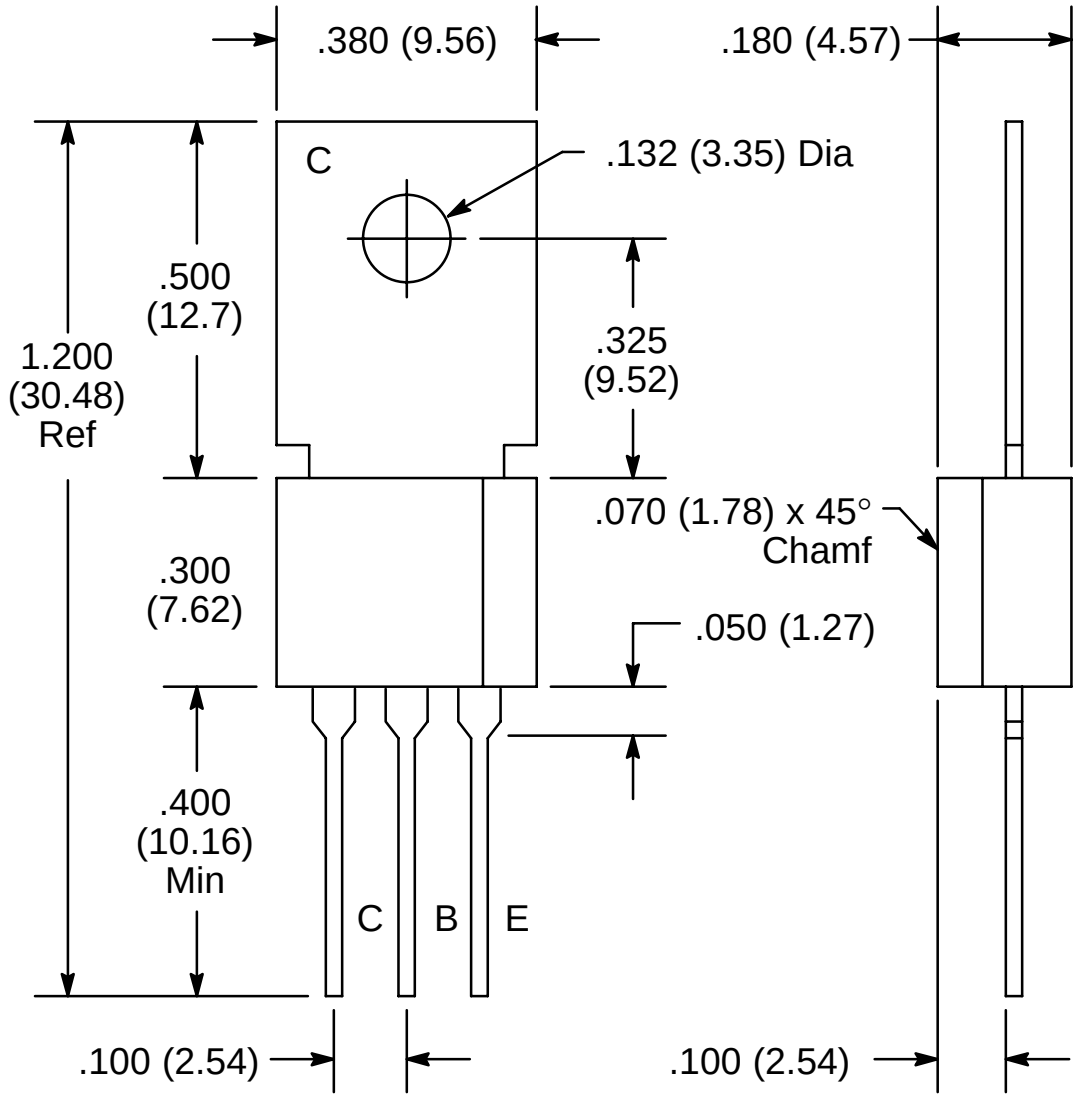
NTE300 (NPN) & NTE307 (PNP)
Silicon Complementary Transistors
Audio Power Amplifier

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector-Base Voltage, V_{CBO} 50V
Collector-Emitter Voltage, V_{CEO} 40V
Emitter-Base Voltage, V_{EBO} 5V
Collector Current, I_C 1.5A
Collector Power Dissipation (T_C = +25°C), P_C 7W
Operating Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . -55° to +150°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = 1mA, I_E = 0	50	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)EBO}$	I_C = 10mA, R_{BE} = ∞	40	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = 1mA, I_C = 0	5	-	-	V
Collector Cutoff Current	I_{CBO}	V_{CB} = 25V, I_E = 0	-	-	1	µA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 5V, I_C = 0	-	-	1	µA
DC Current Gain	h_{FE}	V_{CE} = 4V, I_C = 500mA	55	-	300	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 1A, I_B = 50mA	-	-	1	V
Base-Emitter Voltage	V_{BE}	V_{CE} = 4V, I_C = 50mA	-	0.7	-	V


.380 (9.56)
.180 (4.57)
C
.132 (3.35) Dia
.500
(12.7)
1.200
(30.48)
Ref
.325
(9.52)
.070 (1.78) x 45°
Chamf
.300
(7.62)
.050 (1.27)
.400
(10.16)
Min
C
B
E
.100 (2.54)
.100 (2.54)